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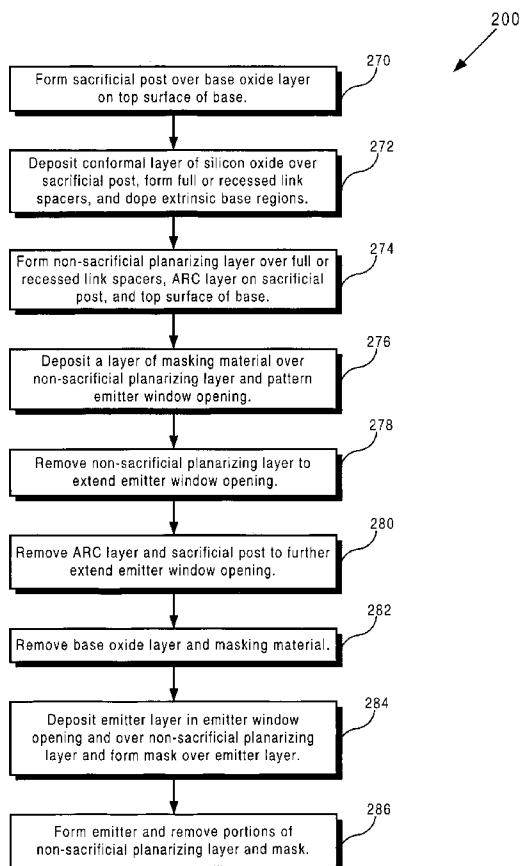
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(54) Title: METHOD FOR FABRICATING A SELF-ALIGNED BIPOLAR TRANSISTOR WITH PLANARIZING LAYER AND RELATED STRUCTURE



(57) Abstract: According to one exemplary embodiment, a bipolar transistor comprises a base having a top surface. The bipolar transistor further comprises first and second link spacers situated on the top surface of the base. The bipolar transistor further comprises a sacrificial post situated on the top surface of the base between the first and second link spacers. The first and second link spacers may have a height, for example, approximately equal to or, in another embodiment, substantially less than a height of the sacrificial post. According to this exemplary embodiment, the bipolar transistor further comprises a non-sacrificial planarizing layer situated over the sacrificial post, first and second link spacers, and base. The non-sacrificial planarizing layer may comprise, for example, silicate glass. The sacrificial planarizing layer may have a height, for example, approximately equal to or, in another embodiment, greater than a height of the first and second link spacers.

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